

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously amended) A dielectric layer fabrication method, comprising the steps of:

- (a) applying a layer of dielectric precursor on a body;
- (b) continuously flowing a precursor reaction catalyst over said layer; and
- (c) completing a precursor reaction to form a dielectric layer.

Claim 2 (previously added) The method of claim 1, wherein:

- (a) said catalyst of step (b) of claim 1 includes ammonia.

Claim 3 (previously added) The method of claim 2, wherein:

- (a) said catalyst of step (a) of claim 2 is a mixture of ammonia and water with a ratio of ammonia to water held constant in time.

Claim 4 (previously added) The method of claim 3, wherein:

- (a) said mixture of step (a) of claim 3 obtains from bubbling ammonia through a water solution of NH_4OH .

Claim 5 (previously added) The method of claim 1, wherein:

- (a) said body of step (a) of claim 1 is within a circular cylindrical chamber; and
- (b) said flowing of step (b) of claim 1 is into said chamber at the circular periphery of said chamber, is radial over said precursor layer to a central axis, and is out of said chamber at said central axis.

Claim 6 (previously added) The method of claim 1, wherein:

(a) said precursor of step (a) of claim 1 includes oligomers polymerized from silicon alkoxides.

Claim 7 (previously added) The method of claim 1, wherein:

(a) said body of step (a) of claim 1 is within a chamber; and

(b) said flowing of step (b) of claim 1 flushes said chamber within a time interval in the range of 1 to 23 seconds.